



SCHOTTKY DIODE MODULE TYPE 800A

Features

High surge Capability
Type 200V V_{RRM}

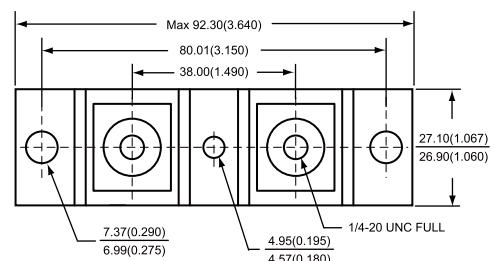
HEAVY TWIN TOWER**Maximum Ratings**

Operating Temperature: -55°C to +150 °C

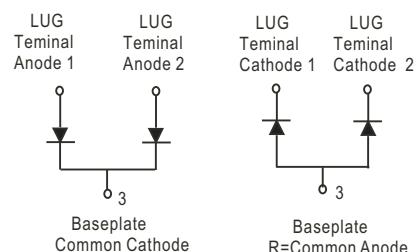
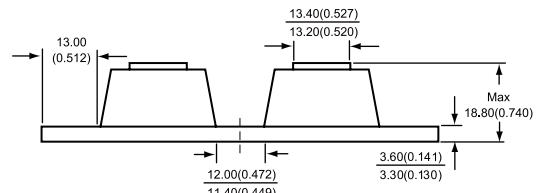
Storage Temperature: -55°C to +150 °C

Dimensions in mm (1 mm = 0.0394")

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBRA801200CT(R)	200V	140V	200V

**Electrical Characteristics @ 25°C Unless Otherwise Specified**

Average Forward Current (Per pkg)	I _{F(AV)}	800A	T _C = 100 °C
Peak Forward Surge Current (Per leg)	I _{FSM}	6200A	8.3ms, half sine
Maximum Instantaneous Forward Voltage (Per leg)	V _F	0.91V	FM=400A; TJ=25 °C
Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage (Per leg)	I _R	5 mA 10 mA 80 mA	T _J = 25 °C T _J = 100 °C T _J = 150 °C
Maximum Thermal Resistance Junction To Case (Per leg)	R _{θjc}	0.25°C/W	



NOTE :

(1) Pulse Test: Pulse Width 300 μ sec, Duty < 2%



DACO SEMICONDUCTOR CO., LTD.

MBRA801200CT(R)

Figure.1-Typical Forward Characteristics

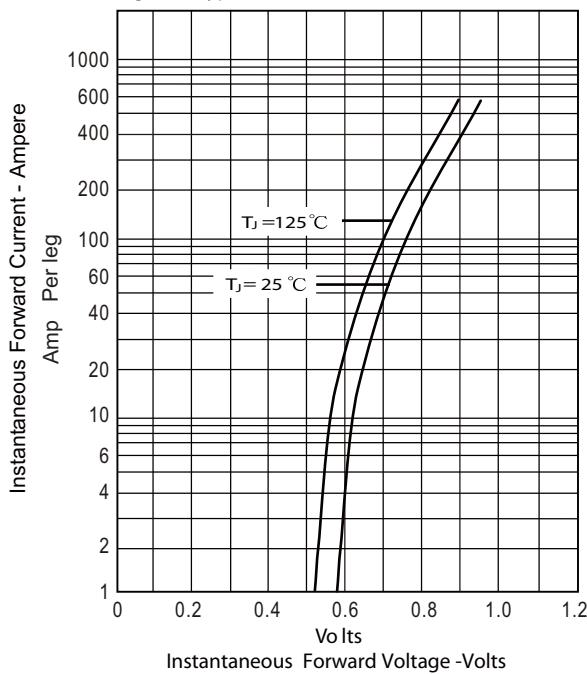


Figure.2-Forward Derating Curve

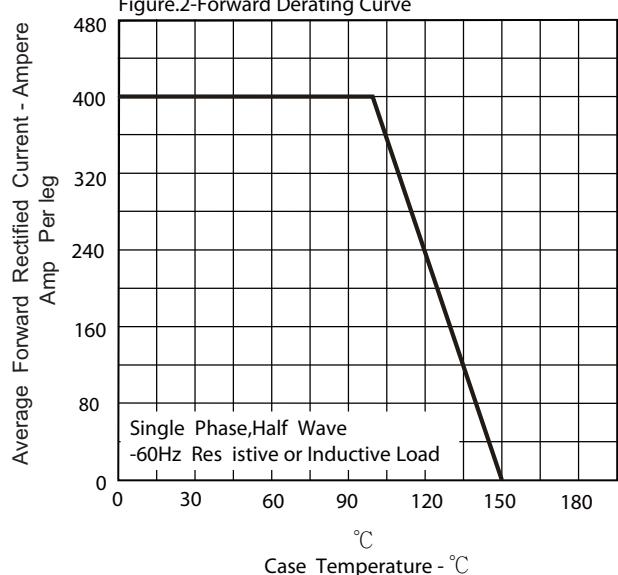


Figure.3-Peak Forward Surge Current

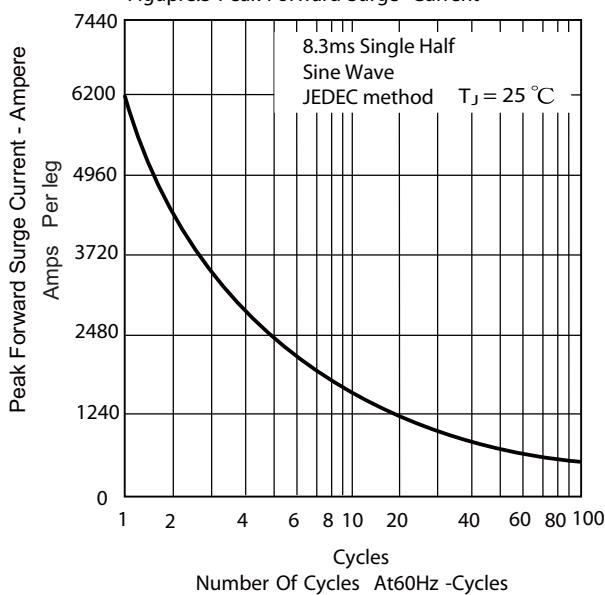


Figure.4-Typical Reverse Characteristics

